

PPSC Physics Full Book

Sr	Questions	Answers Choice
1	at room temperature the p.d. between the two sides of depletion region for silicon is of the order of.	A. 0.3 V B. 0.5 V C. 0.7 V D. 0.9 V
2	A charge less region which separates p-type and n-type semiconductors in a p-n junction is known as.	A. Polar region B. Null region C. Depletion region D. Neutral region
3	The current passing across a p-n junction due to minority charge carriers is called	A. Reverse current B. Forward current C. Leakage current D. Both a and b
4	A p-type material is formed then a semiconductor is doped with	A. Trivalent impurity B. Tetravalent impurity C. All of above D. A material having excess of free electrons
5	In a n-type material there is an excess of.	A. Free electrons B. Holes C. Quarks D. Measons
6	In half wave rectifier the rms value of A.C. component of the wave is.	A. More than A.C. Value B. Less than D.C. value C. Same as that of D.C. D. Not detectable
7	Why is an oxide coated filament used in vacuum tube.	A. It has a longer lime B. It can with stand high C. It emit electrons at low temperature D. It reduces the effect of space charge
8	Where is the velocity of electrons maximum in a diode.	A. Near the cathode B. Near the anode C. In the space ini between the two electrode. D. It is same throughout the tube
9	A vacuum diode conducts when plate	A. Is negative w.r.t cathode B. Is positive w.r.t. cathode C. and cathode are at the same potential D. Resistance is less
10	Which of the following material could be used for a high vacuum, high voltage tube.	A. Thoriated tungsten B. Tungsten C. Copper D. Cesium
11	The thermionic current increases when	A. Area of filament is decreased B. Area of filament is increased C. Temperature is decreased D. Work function is increased
12	Efficiency of a half wave recitifier is.	A. Almost negigible B. More than full wave rectifier C. Less than full wave rectifier D. Equal to full wave rectifier
13	When forwarded bias is applied to a junction diode it.	A. Increases the potential barrier B. Decreases the potential barrier C. Reduces the majority carrier current to zero D. Reduces the minority carrier current to zero
14	Which of the following is not an application of diodes.	A. A filters B. Bridge rectifier C. Voltage divider D. None of these

		C. Half wave rectifier D. Full wave rectifier
15	Since a diode permits the flow of current only in one direction so it can be used as.	A. An oscillator B. A rectifier C. A phot deflector D. A transistor
16	What for is semiconductor diode used.	A. To convert D.C. to A.C. B. To convert A.C. to D.C. C. To increase voltage D. To decrease voltage
17	A forward based p-n semiconductor diode is called.	A. Photodiode B. Photovoltaic cell C. Amplifier D. Light emitted diode
18	If we use two diodes and a centre tapped transformer we will get.	A. A transistor B. An amplifier C. A half wave rectifier D. A full wave rectifier
19	Photo diodes are used as	A. Optical fibre receivers B. Automatic switching C. Logic circuits D. All of the above
20	The eight most common element in the universe by mass is	A. Ge B. C C. Si D. As
21	Pure silicon has valence electrons	A. 1 B. 2 C. 3 D. 4
22	The typical value of forbidden energy gap in germanium is.	A. 0.7 eV B. 1.0 eV C. 1.4 eV D. 10 eV
23	Which one is not a semiconductor.	A. Go As B. Ge C. Sc D. In
24	The most common trivalent impurities are	A. Boron , indium B. Arsenic, indium C. Arsenic, Antimony D. Aluminium, Boron
25	With increase in temperature the electrical conductivity of intrinsic conductors.	A. Increases B. Decreases C. Remain unaffected D. First increases then decreases
26	In a half wave rectifier the rms value of the A.C. component of the wave is.	A. Less than D.C. value B. Greater than D.C. value C. Equal to D.C. value D. Zero
27	Select the one that is not a donor	A. P B. AS C. Sb D. In
28	Which one of the following materials has negative temperature coefficient.	A. Conductors B. Semiconductors C. Insulators D. Covalent bonds
29	A single silicon photovoltaic cell produces a current of the order of.	A. A few milliamperes B. 10^{2} A C. 10^{3} A D. 10^{4} A
30	A single silicon photovoltaic cell produces a voltage of the order of.	A. 0.3 V B. 0.6 V C. 0.9 V D. 1.2 V